

CONTACT PROCESS AND STRUCTURE FOR A SEMICONDUCTOR DEVICE

5

ABSTRACT OF THE DISCLOSURE

A contact process for a semiconductor device containing a base region of a first conductivity type formed on a 10 semiconductor substrate comprises formation of a first shallow layer of the first conductivity type on the base region, deposition of an insulator on the first shallow layer, etching the insulator and first shallow layer to form a contact hole, thermally driving the first shallow layer more deeply into said base region, formation of a 15 second shallow layer of a second conductivity type on the base region at the bottom of the contact hole, filling a metal in the contact hole to contact the sidewall of the first shallow layer and the second shallow layer.